

April 1995

50A, 1200V Hyperfast Diode

Features

- Hyperfast with Soft Recovery <85ns
- Operating Temperature +175°C
- Reverse Voltage 1200V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Description

The RHRG50120 (TA49100) are hyperfast diodes with soft recovery characteristics ($t_{RR} < 85\text{ns}$). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

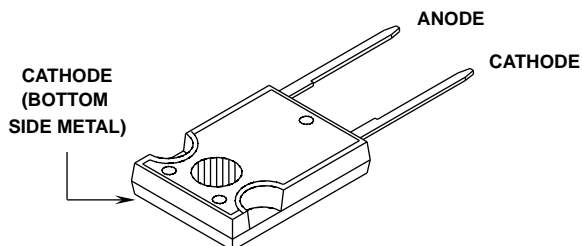
PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RHRG50120	TO-247	RHRG50120

NOTE: When ordering, use the entire part number.

Package

JEDEC STYLE TO-247



Symbol



Absolute Maximum Ratings $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

	RHRG50120	UNITS
Peak Repetitive Reverse Voltage.....	1200	V
Working Peak Reverse Voltage.....	1200	V
DC Blocking Voltage.....	1200	V
Average Rectified Forward Current..... ($T_C = 50^\circ\text{C}$)	50	A
Repetitive Peak Surge Current..... (Square Wave, 20kHz)	100	A
Nonrepetitive Peak Surge Current..... (Halfwave, 1 Phase, 60Hz)	500	A
Maximum Power Dissipation.....	150	W
Avalanche Energy (See Figures 10 and 11).....	50	mJ
Operating and Storage Temperature.....	-65 to +175	$^\circ\text{C}$

Specifications RHRG50120

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	LIMITS			UNITS
		MIN	TYP	MAX	
V_F	$I_F = 50\text{A}$, $T_C = +25^\circ\text{C}$	-	-	3.2	V
	$I_F = 50\text{A}$, $T_C = +150^\circ\text{C}$	-	-	2.6	V
I_R	$V_R = 1200\text{V}$, $T_C = +25^\circ\text{C}$	-	-	500	μA
	$V_R = 1200\text{V}$, $T_C = +150^\circ\text{C}$	-	-	1.0	mA
t_{RR}	$I_F = 1\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	85	ns
	$I_F = 50\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
t_A	$I_F = 50\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	50	-	ns
t_B	$I_F = 50\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	40	-	ns
Q_{RR}	$I_F = 50\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	240	-	nC
C_J	$V_R = 10\text{V}$, $I_F = 0\text{A}$	-	150	-	pF
$R_{\theta JC}$		-	-	1.0	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (See Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy. (See Figures 10 and 11).

pw = pulse width.

D = duty cycle.

V_1 AMPLITUDE CONTROLS I_F
 V_2 AMPLITUDE CONTROLS dI_F/dt
 L_1 = SELF INDUCTANCE OF
 $R_4 + L_{\text{LOOP}}$

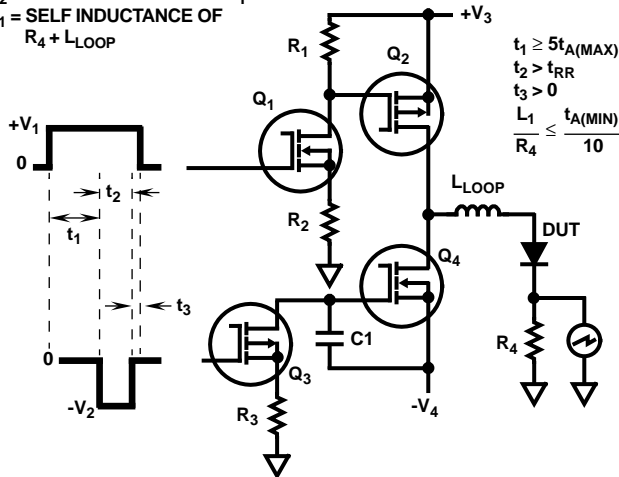


FIGURE 1. t_{RR} TEST CIRCUIT

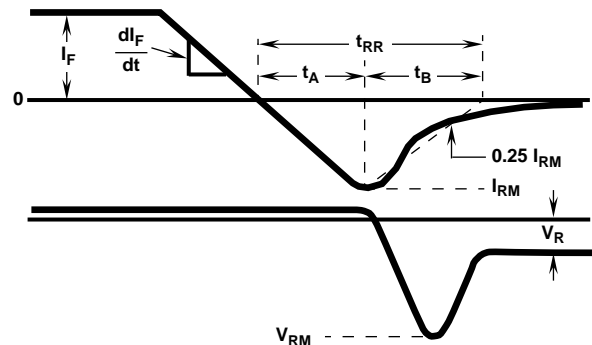


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

Typical Performance Curves

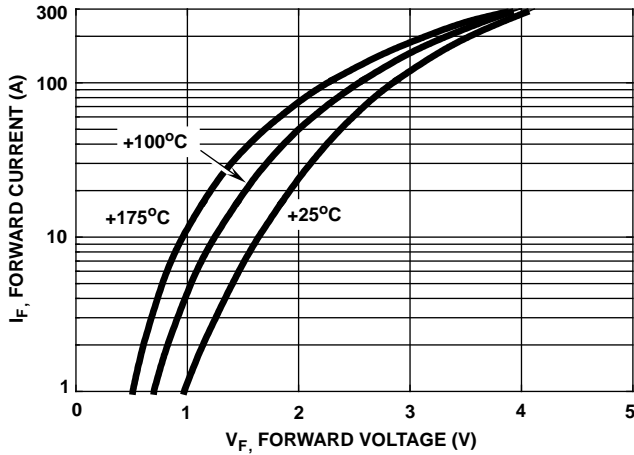


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

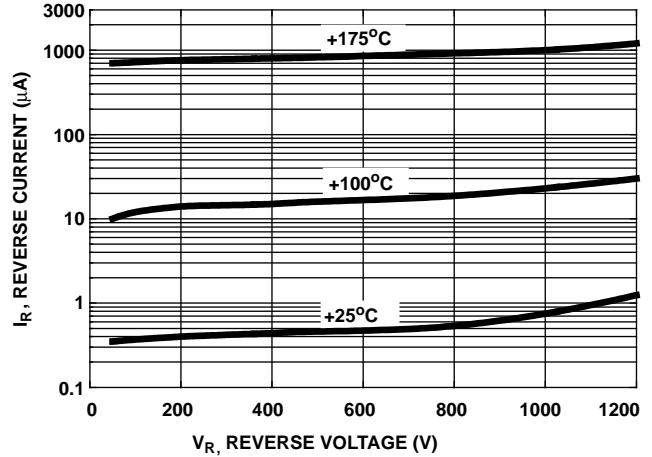


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

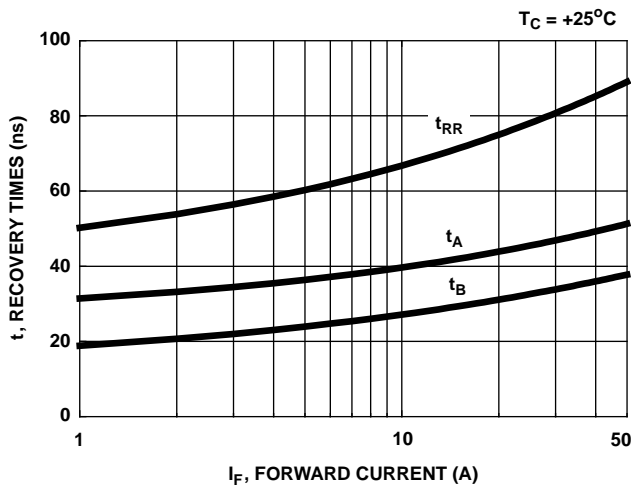


FIGURE 5. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +25°C

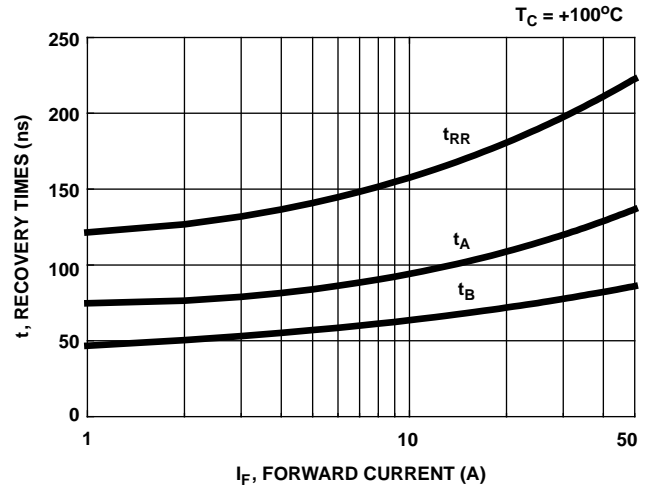


FIGURE 6. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +100°C

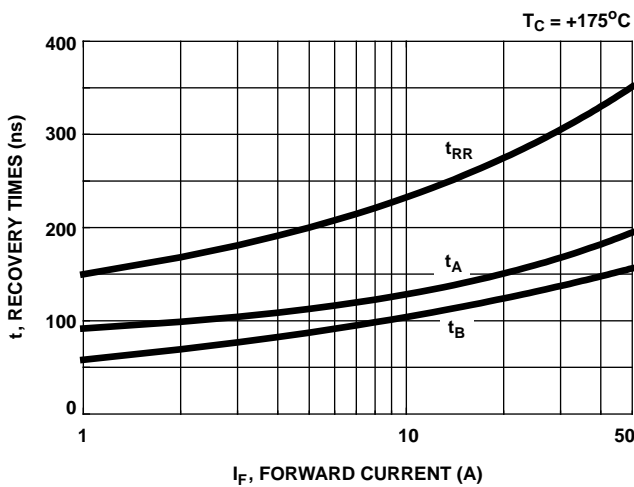


FIGURE 7. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +175°C

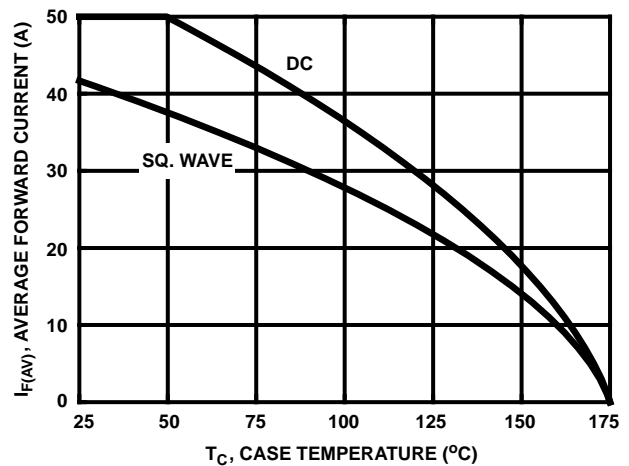


FIGURE 8. CURRENT DERATING CURVE

Typical Performance Curves (Continued)

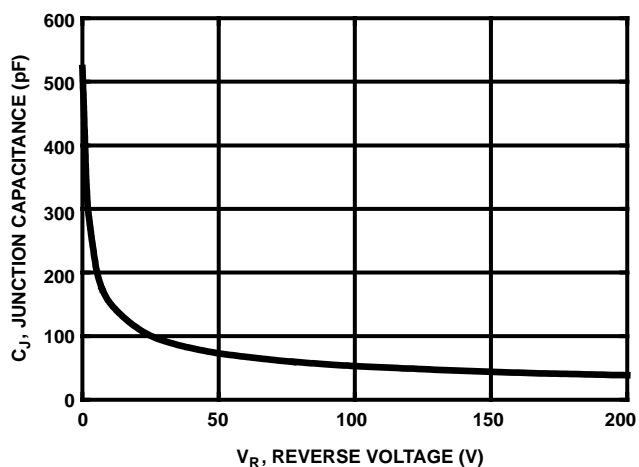


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuit and Waveforms

$$I_{MAX} = 1A$$

$$L = 40mH$$

$$R < 0.1\Omega$$

$$E_{AVL} = 1/2LI^2 [V_{AVL}/(V_{AVL} - V_{DD})]$$

Q₁ AND Q₂ ARE 1000V MOSFETs

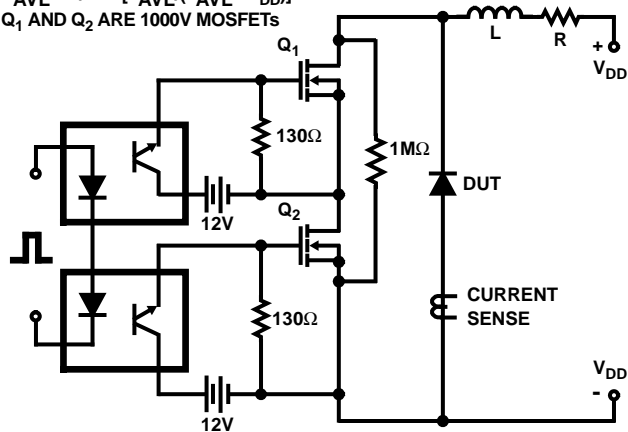


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

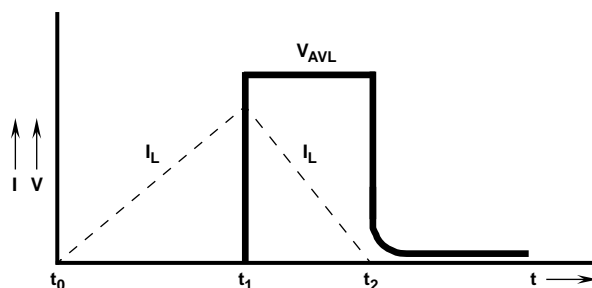


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS